

## **FJP5027**

## High Voltage and High Reliability

- High Speed Switching
- Wide SOA



1.Base 2.Collector 3.Emitter

## **NPN Silicon Transistor**

## Absolute Maximum Ratings $T_C=25^{\circ}C$ unless otherwise noted

Symbol	Parameter	Value	Units
V <sub>CBO</sub>	Collector-Base Voltage	1100	V
V <sub>CEO</sub>	Collector-Emitter Voltage	800	V
V <sub>EBO</sub>	Emitter-Base Voltage	7	V
I <sub>C</sub>	Collector Current (DC)	3	Α
I <sub>CP</sub>	Collector Current (Pulse)	10	Α
I <sub>B</sub>	Base Current	1.5	Α
P <sub>C</sub>	Collector Dissipation ( T <sub>C</sub> =25°C)	50	W
T <sub>J</sub>	Junction Temperature	150	°C
T <sub>STG</sub>	Storage Temperature	- 55 ~ 150	°C

## Electrical Characteristics $T_C=25$ °C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
BV <sub>CBO</sub>	Collector-Base Breakdown Voltage	$I_C = 1 \text{mA}, I_E = 0$	1100			V
BV <sub>CEO</sub>	Collector-Emitter Breakdown Voltage	$I_C = 5mA, I_B = 0$	800			V
BV <sub>EBO</sub>	Emitter-Base Breakdown Voltage	$I_E = 1 \text{mA}, I_C = 0$	7			V
V <sub>CEX</sub> (sus)	Collector-Emitter Sustaining Voltage	$I_C = 1.5A$ , $I_{B1} = -I_{B2} = 0.3A$ L = 2mH, Clamped	800			V
I <sub>CBO</sub>	Collector Cut-off Current	$V_{CB} = 800 V, I_{E} = 0$			10	μΑ
I <sub>EBO</sub>	Emitter Cut-off Current	$V_{EB} = 5V, I_{C} = 0$			10	μΑ
h <sub>FE1</sub>	DC Current Gain	$V_{CE} = 5V, I_{C} = 0.2A$	10		40	
h <sub>FE2</sub>		$V_{CE} = 5V, I_{C} = 1A$	8			
V <sub>CE</sub> (sat)	Collector-Emitter Saturation Voltage	$I_C = 1.5A, I_B = 0.3A$			2	V
V <sub>BE</sub> (sat)	Base-Emitter Saturation Voltage	$I_C = 1.5A, I_B = 0.3A$			1.5	V
C <sub>ob</sub>	Output Capacitance	$V_{CB} = 10V, I_E = 0, f = 1MHz$		60		pF
f <sub>T</sub>	Current Gain Bandwidth Product	$V_{CE} = 10V, I_{C} = 0.2A$		15		MHz
t <sub>ON</sub>	Turn On Time	V <sub>CC</sub> = 400V			0.5	μs
t <sub>STG</sub>	Storage Time	$I_C = 5I_{B1} = -2.5I_{B2} = 2A$			3	μs
t <sub>F</sub>	Fall Time	$R_L = 200\Omega$			0.3	μs

## $\mathbf{h}_{\text{FE}}$ Classification

Classification	N	R	0
h <sub>FE1</sub>	10 ~ 20	15 ~ 30	20 ~ 40

# **Typical Characteristics**

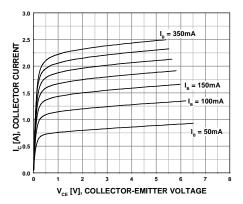


Figure 1. Static Characteristic

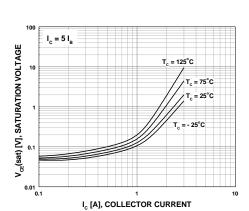


Figure 3. Base-Emitter Saturation Voltage Collector-Emitter Saturation Voltage

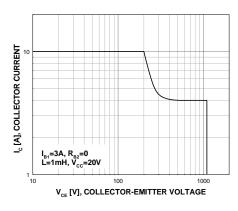


Figure 5. Switching Time

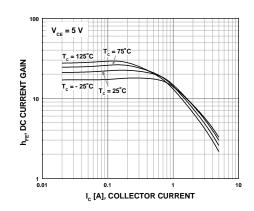


Figure 2. DC current Gain

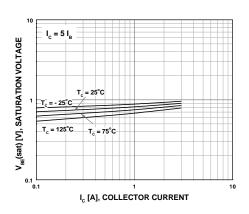


Figure 4. Base-Emitter On Voltage

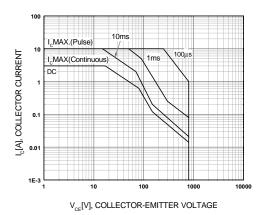
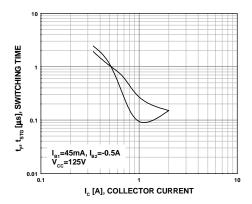


Figure 6. Safe Operating Area

# Typical Characteristics (Continued)



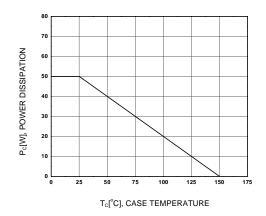
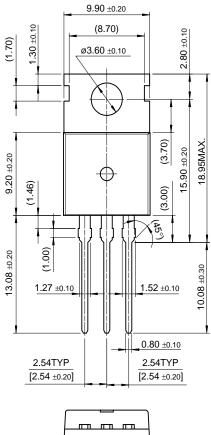


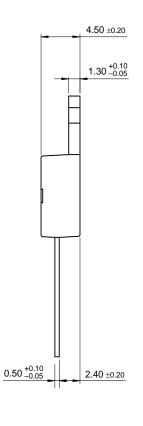
Figure 7. Resistive Load Switching Characteristics

Figure 8. Power Derating

# **Package Dimensions**

# TO-220





10.00 ±0.20

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